

IN THE DRAWINGS:

Please note the changes to Fig. 3 in which the labels have been reversed for the curves initially designated as "BASE (p)" and "LINK BASE LAYER (p)," and the changes to Figs. 4A to 4C and 5A to 5C which are to be labeled as -- (PRIOR ART) --.

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 1, line 8, with the following rewritten paragraph:

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a

--Recently, in the field of semiconductor devices such as LSIs, there have been strong demands toward enhancement in performance of bipolar transistors. The enhancement in the performance of bipolar transistors can be achieved by the shortening of a base transit time due to shortening of a base thickness by lowering of a base resistance, and by reduction of a parasitic capacitance represented by a base-collector capacitance.--

Please replace the paragraph beginning at page 2, line 5, with the following rewritten paragraph:

12 Contd

--The bipolar transistor having the above-described structure is fabricated in the following procedures.